

Ordering number : ENN7511

PNP Epitaxial Planar Silicon Transistor

**30A01S**

## Low-Frequency General-Purpose Amplifier Applications

### Applications

- Low-frequency power amplifier, muting circuit.

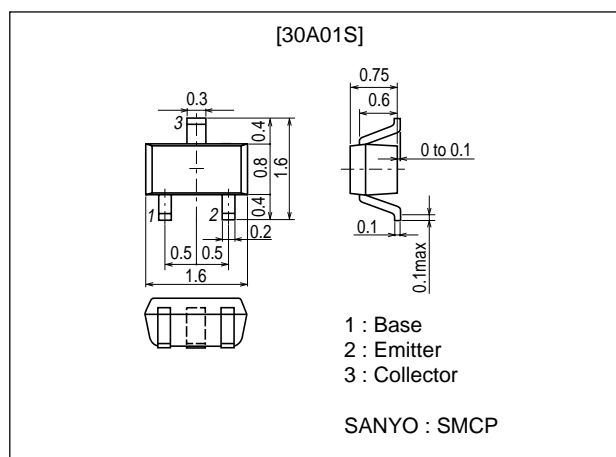
### Features

- Large current capacity.
- Low collector-to-emitter saturation voltage (resistance).  
RCE(sat) typ=0.67Ω[IC=0.3A, IB=15mA].
- Ultrasmall package facilitates miniaturization in end products.
- Small ON-resistance (Ron).

### Package Dimensions

unit : mm

2106A



### Specifications

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CB0</sub>		-30	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>		-30	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		-5	V
Collector Current	I <sub>C</sub>		-300	mA
Collector Current (Pulse)	I <sub>CP</sub>		-600	mA
Collector Dissipation	P <sub>C</sub>	Mounted on a glass epoxy board (20X30X1.6mm).	200	mW
Junction Temperature	T <sub>J</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =-30V, I <sub>E</sub> =0			-0.1	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V, I <sub>C</sub> =0			-0.1	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-10mA	200		500	
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-50mA		520		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, f=1MHz		3		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-5mA		-110	-220	mV
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-5mA		-0.9	-1.2	V

Marking : XQ

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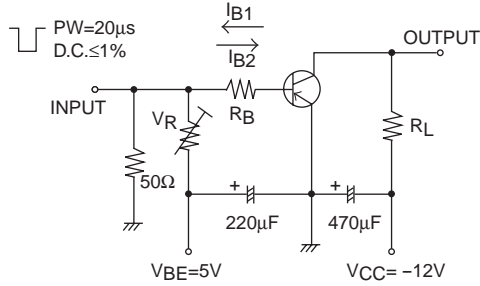
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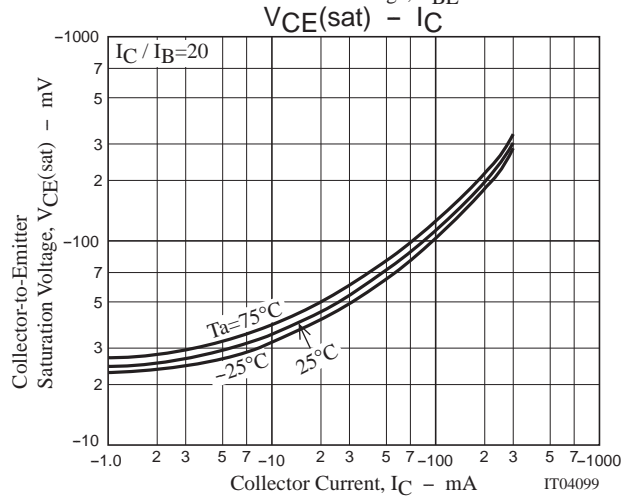
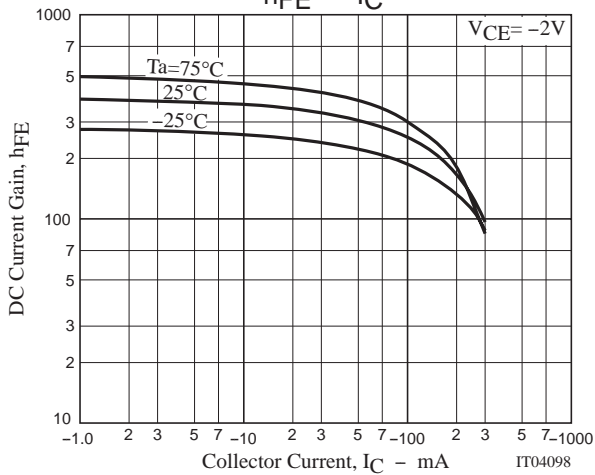
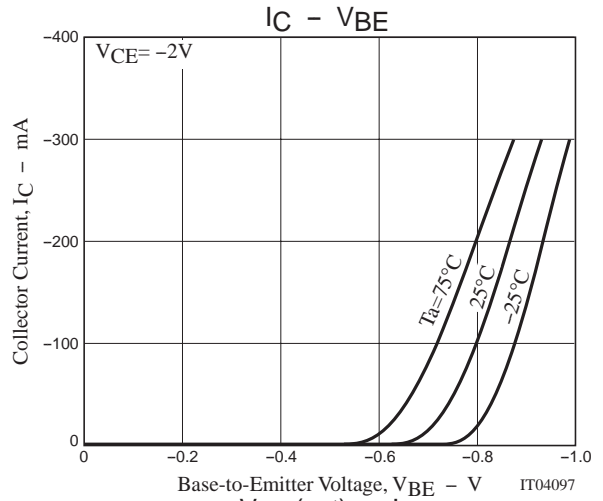
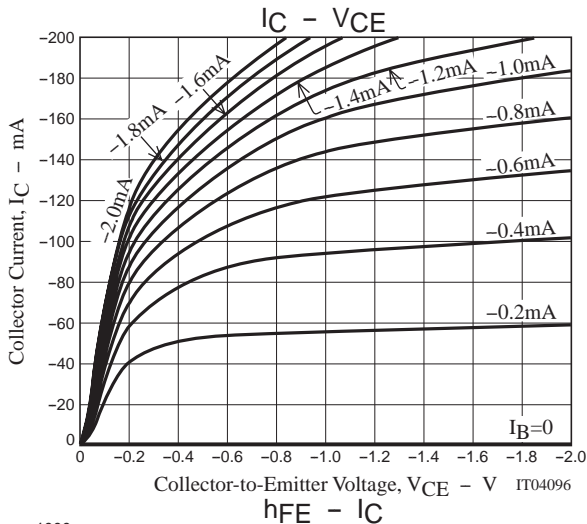
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-30			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, R_{BE} = \infty$	-30			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Turn-ON Time	$t_{on}$	See specified Test Circuit.		39		ns
Storage Time	$t_{stg}$	See specified Test Circuit.		200		ns
Fall Time	$t_f$	See specified Test Circuit.		48		ns

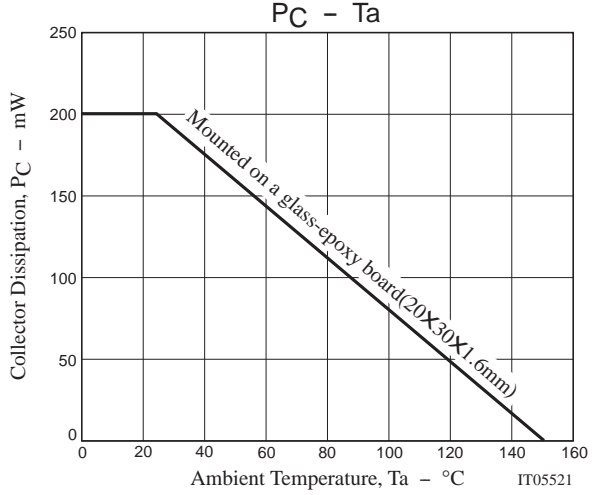
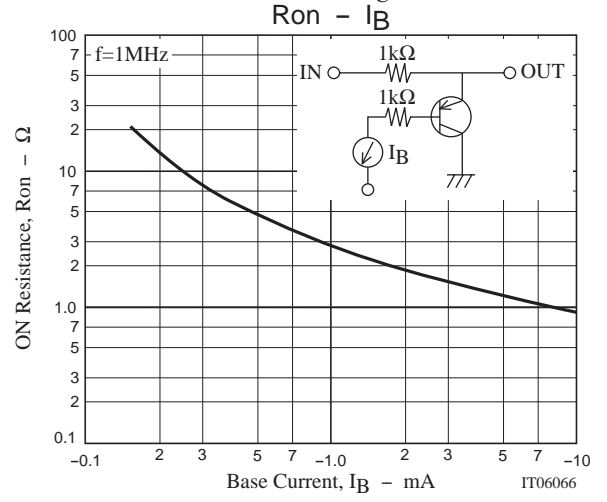
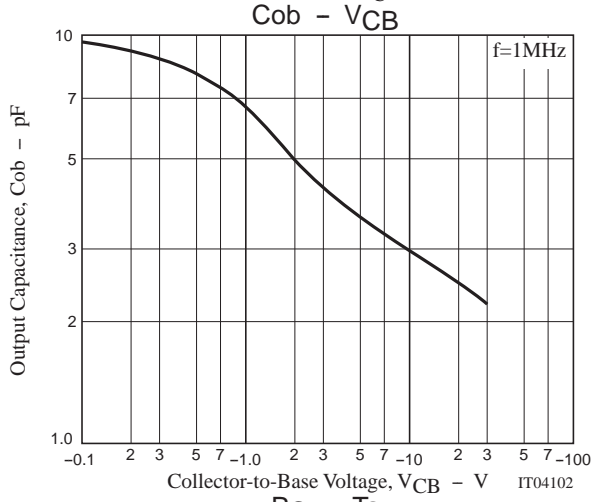
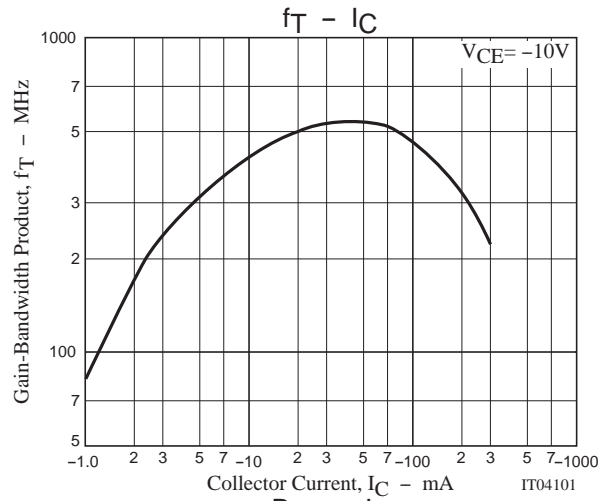
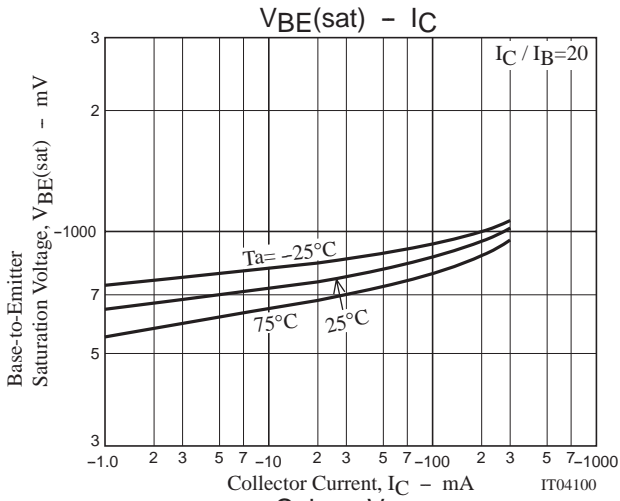
## Switching Time Test Circuit



$$I_C = 20I_{B1} = -20I_{B2} = -100mA$$



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